ABSTRACT

METHOD OF MANUFACTURING
A SEMICONDUCTOR STRUCTURE

There is provided a method of manufacturing a field effect transistor (FET) (100) that includes the steps of forming a gate structure (175) on a semiconductor substrate (105), and forming a recess (160) in the substrate and embedding a second semiconductor material (165) in the recess. The gate structure includes a gate dielectric layer (115), conductive layers (120, 130) and an insulating layer (125). Forming said gate structure includes a step of recessing the conductive layer (130) in the gate structure, and the steps of recessing the conductive layer and forming the recess (160) in the substrate are performed in a single step. There is also provided a FET device.

Fig. 12